



PMEG3010AESA

30 V, 1 A low VF MEGA Schottky barrier rectifier

3 August 2015

Preliminary data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a leadless ultra small DSN1006U-2 (SOD995) Surface-Mounted Device (SMD) package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 1$ A
- Reverse voltage: $V_R \leq 30$ V
- Low forward voltage, typical: $V_F = 415$ mV
- Low reverse current, typical: $I_R = 300$ μ A
- Package height typ. 270 μ m

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

4. Quick reference data

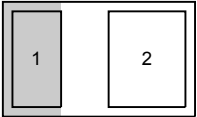
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 145$ °C; square wave	-	-	1	A
V_R	reverse voltage	$T_j = 25$ °C	-	-	30	V
V_F	forward voltage	$I_F = 1$ A; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_j = 25$ °C	-	415	480	mV
I_R	reverse current	$V_R = 20$ V; $t_p \leq 3$ ms; $\delta \leq 0.3$; $T_j = 25$ °C	-	60	255	μ A
		$V_R = 30$ V; $t_p \leq 3$ ms; $\delta \leq 0.3$; $T_j = 25$ °C	-	300	1250	μ A



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	 Transparent top view DSN1006U-2 (SOD995)	 <i>sym001</i>
2	A	anode		

[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3010AESA	DSN1006U-2	leadless ultra small package; 2 terminals; body 1.0 x 0.6 x 0.27 mm	SOD995

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3010AESA	3B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	30	V
I_F	forward current	$T_{sp} \leq 140\text{ }^{\circ}\text{C}; \delta = 1$		-	1.4	A
$I_{F(AV)}$	average forward current	$\delta = 0.5; f = 20\text{ kHz}; T_{amb} \leq 115\text{ }^{\circ}\text{C};$ square wave	[1]	-	1	A
		$\delta = 0.5; f = 20\text{ kHz}; T_{sp} \leq 145\text{ }^{\circ}\text{C};$ square wave		-	1	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}; \delta \leq 0.25$		-	4	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}; T_{j(init)} = 25\text{ }^{\circ}\text{C};$ square wave		-	10	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	[2]	-	0.69	W
			[3]	-	1.19	W
			[1]	-	1.78	W
T_j	junction temperature			-	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	150	$^{\circ}\text{C}$

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3 , standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm^2 each.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	180	K/W
			[1][3]	-	-	105	K/W
			[1][4]	-	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	15	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of anode tab.

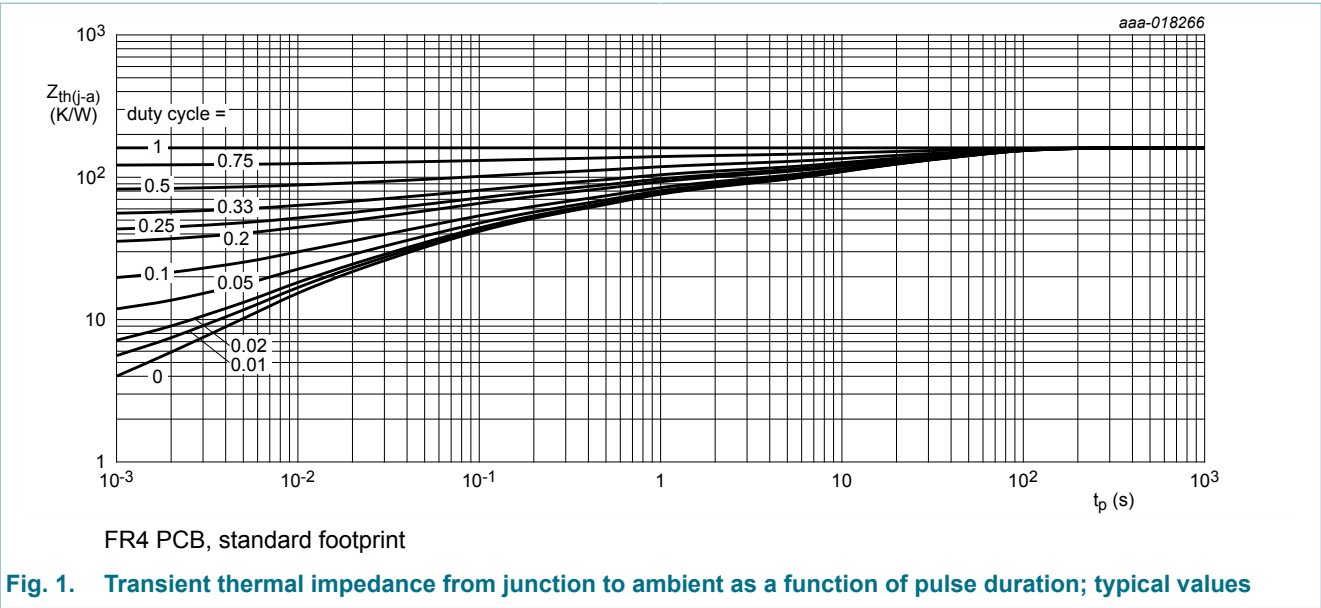
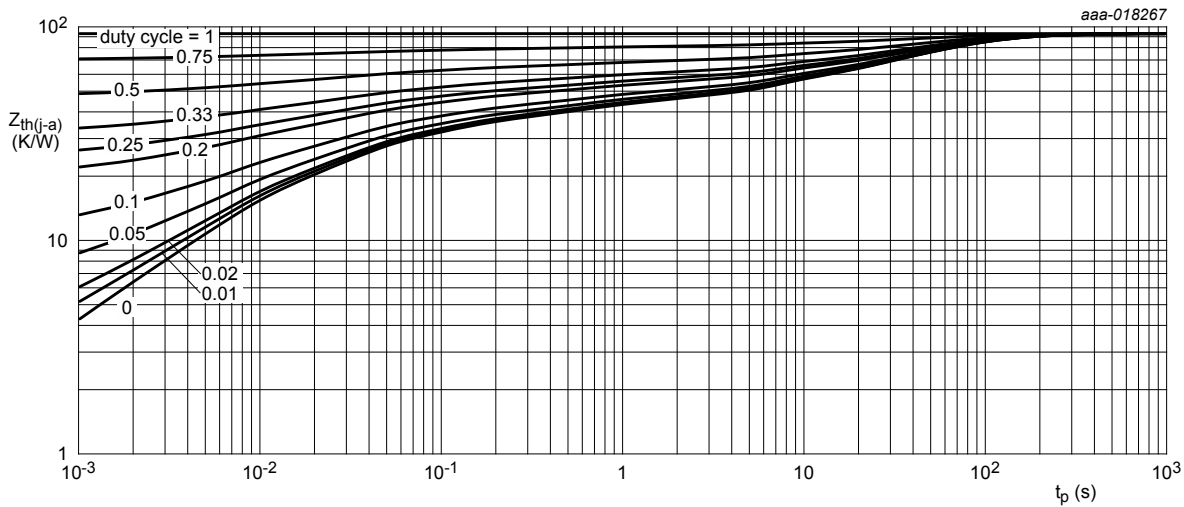
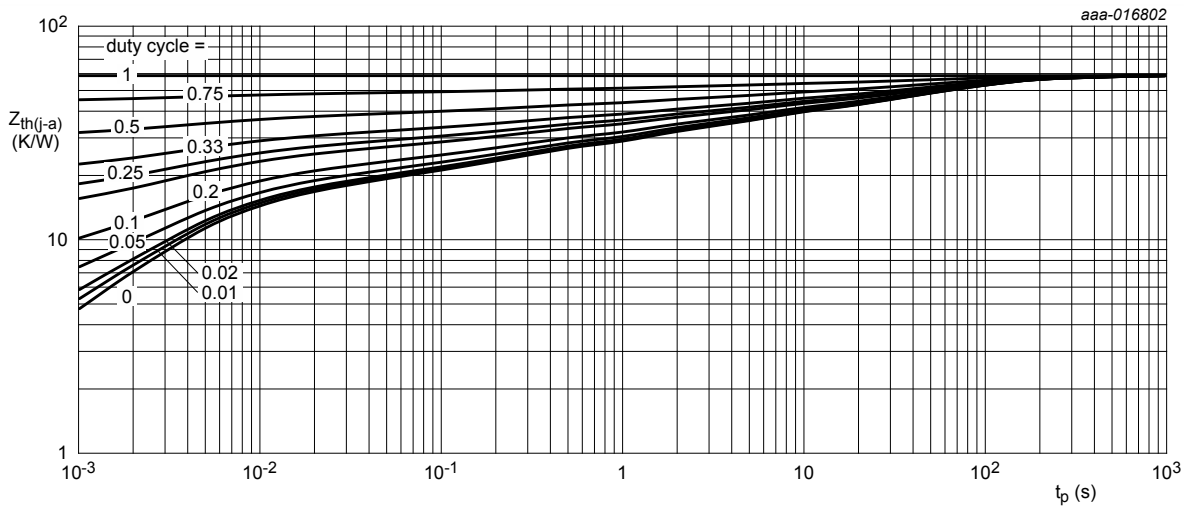


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm² each

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



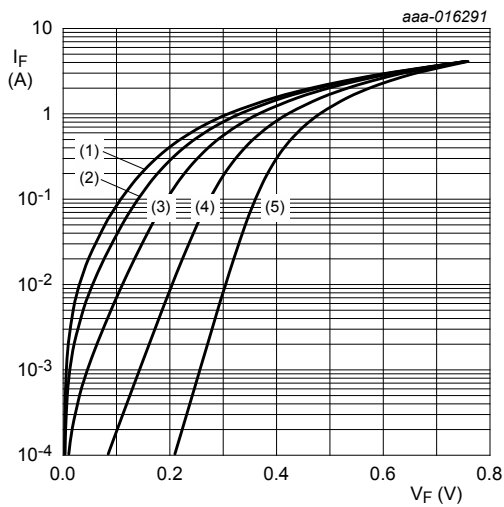
Ceramic PCB, Al₂O₃, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

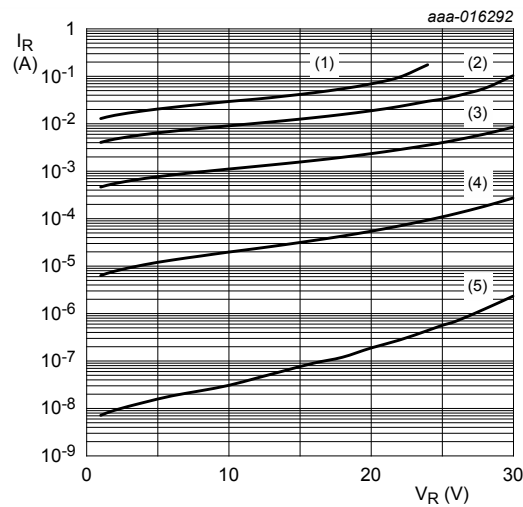
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 10 \text{ mA}$; $t_p = 300 \text{ } \mu\text{s}$; $\delta = 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	30	-	-	V
V_F	forward voltage	$I_F = 1 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	140	-	mV
		$I_F = 10 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	200	-	mV
		$I_F = 100 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	270	325	mV
		$I_F = 200 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	300	-	mV
		$I_F = 500 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	355	405	mV
		$I_F = 700 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	380	-	mV
		$I_F = 1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ } ^\circ\text{C}$	-	415	480	mV
I_R	reverse current	$V_R = 5 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_J = 25 \text{ } ^\circ\text{C}$	-	13	-	μA
		$V_R = 10 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_J = 25 \text{ } ^\circ\text{C}$	-	22	90	μA
		$V_R = 20 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_J = 25 \text{ } ^\circ\text{C}$	-	60	255	μA
		$V_R = 30 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_J = 25 \text{ } ^\circ\text{C}$	-	300	1250	μA
C_d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_J = 25 \text{ } ^\circ\text{C}$	-	86	-	pF
		$V_R = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_J = 25 \text{ } ^\circ\text{C}$	-	32	-	pF
t_{rr}	reverse recovery time	$I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(\text{meas})} = 0.1 \text{ A}$; $T_J = 25 \text{ } ^\circ\text{C}$	-	3.5	-	ns



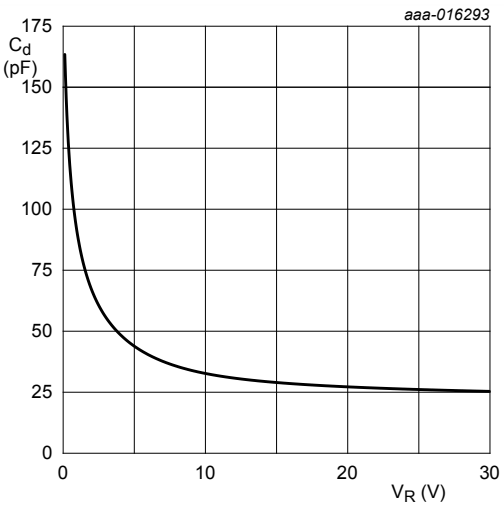
pulsed condition
(1) $T_j = 150^\circ\text{C}$
(2) $T_j = 125^\circ\text{C}$
(3) $T_j = 85^\circ\text{C}$
(4) $T_j = 25^\circ\text{C}$
(5) $T_j = -40^\circ\text{C}$

Fig. 4. Forward current as a function of forward voltage; typical values



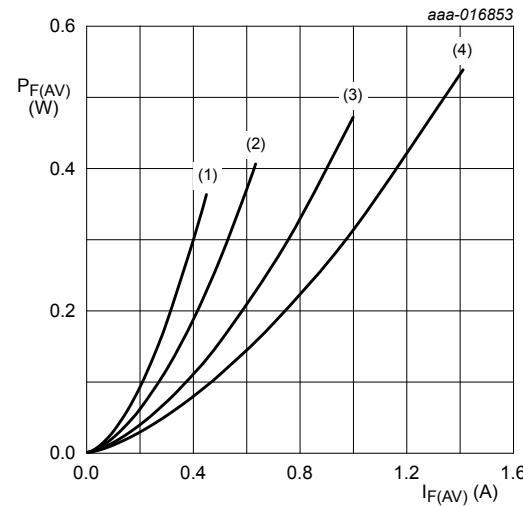
pulsed condition
(1) $T_j = 150^\circ\text{C}$
(2) $T_j = 125^\circ\text{C}$
(3) $T_j = 85^\circ\text{C}$
(4) $T_j = 25^\circ\text{C}$
(5) $T_j = -40^\circ\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}$; $T_{\text{amb}} = 25^\circ\text{C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



$T_j = 150^\circ\text{C}$
(1) $\delta = 0.1$
(2) $\delta = 0.2$
(3) $\delta = 0.5$
(4) $\delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

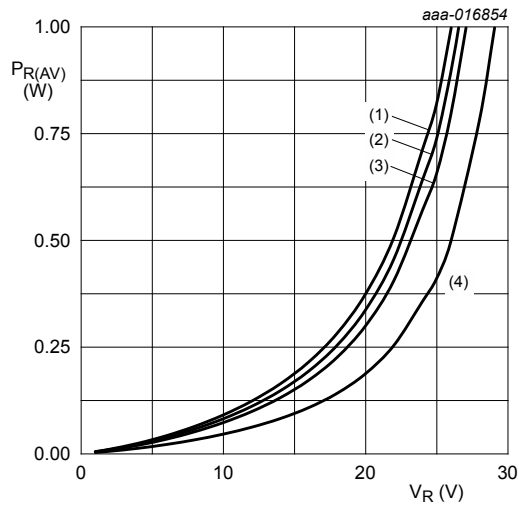


Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values

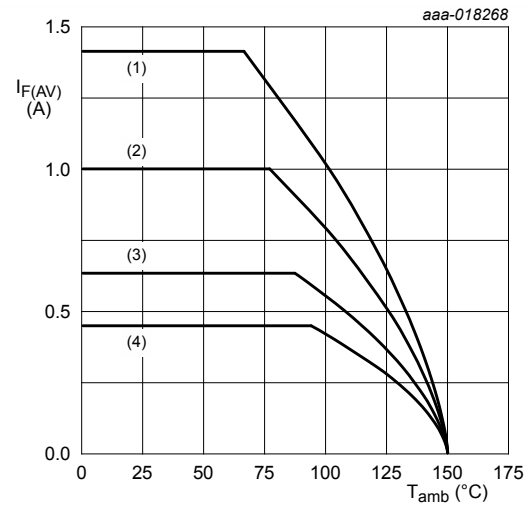


Fig. 9. Average forward current as a function of ambient temperature; typical values

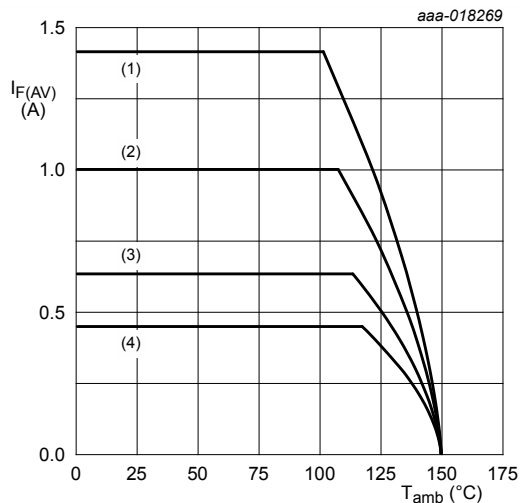


Fig. 10. Average forward current as a function of ambient temperature; typical values

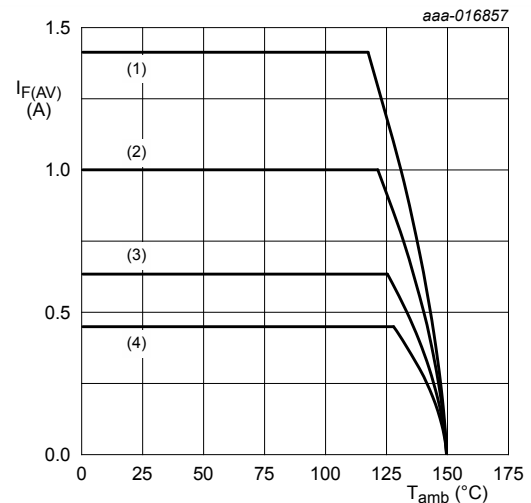
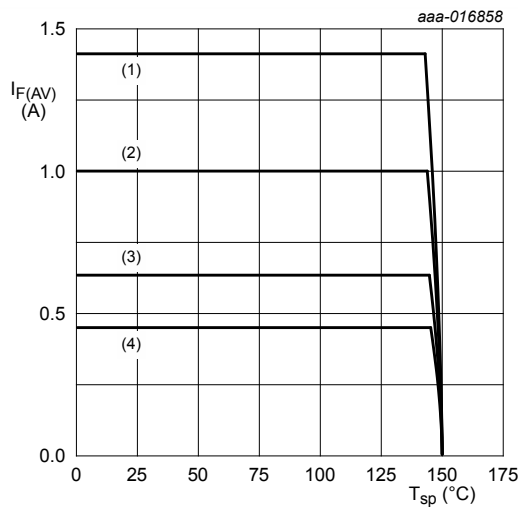


Fig. 11. Average forward current as a function of ambient temperature; typical values



$T_J = 150\text{ }^{\circ}\text{C}$
(1) $\delta = 1$ (DC)
(2) $\delta = 0.5$; $f = 20\text{ kHz}$
(3) $\delta = 0.2$; $f = 20\text{ kHz}$
(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 12. Average forward current as a function of solder point temperature; typical values

11. Test information

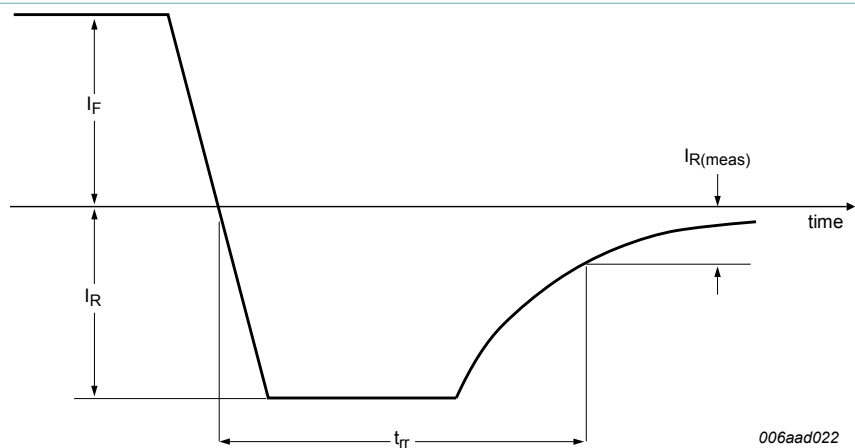


Fig. 13. Reverse recovery definition; step recovery

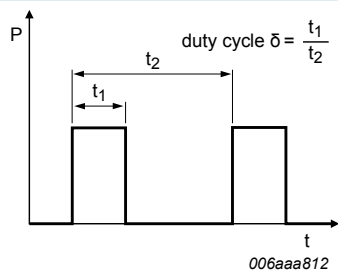


Fig. 14. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:
 $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

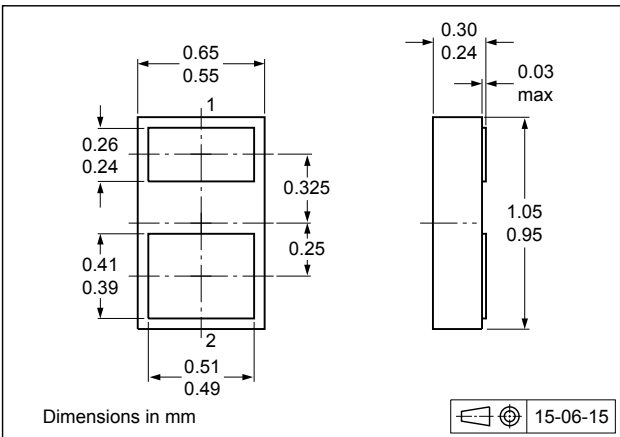


Fig. 15. Package outline DSN1006U-2 (SOD995)

13. Soldering

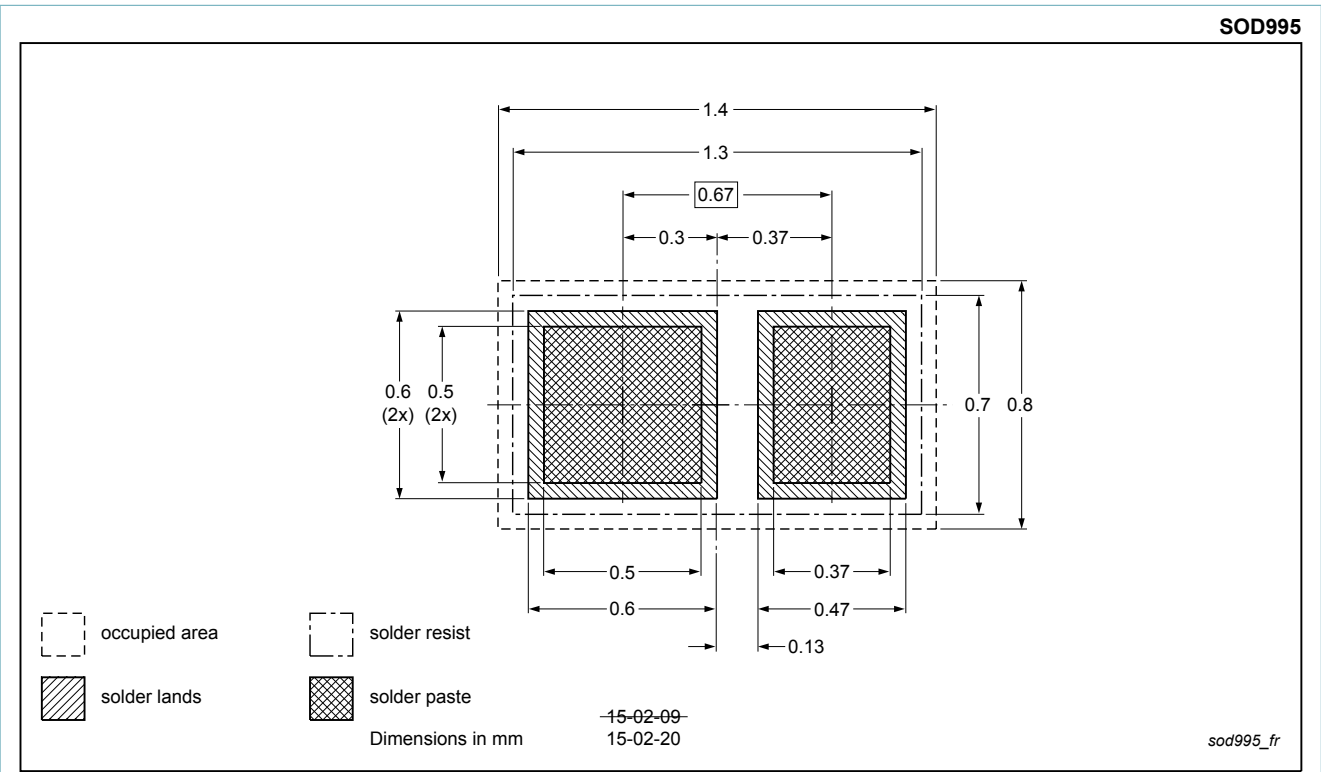


Fig. 16. Reflow soldering footprint for DSN1006U-2 (SOD995)

14. Mounting

SOD995 is an ultra small Discretes Silicon No-leads (DSN) package allowing maximized utilization of the package area for active silicon. Due to the special product design, NXP investigated the board assembly process parameters. In order to have an optimum soldering quality, NXP advises to follow the assembly recommendations explained in [AN11689](#).

15. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3010AESA v.1	20150803	Preliminary data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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